

Basics of Test Technology

Adit D. Singh

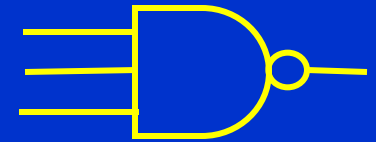
**Electrical & Computer Engineering
Auburn University**

Introduction

- **Many integrated circuits contain fabrication defects upon manufacture**
- **Only 20-60% for high end circuits manufactured may be defect free**
- **ICs must be carefully tested to screen out faulty parts before integration in systems**
- **Latent faults that cause early life failure must also be screened out through “burn-in” stress tests**

IC Testing is a Difficult Problem

- Need $2^3 = 8$ input patterns to exhaustively test a 3-input NAND
- 2^N tests needed for N-input circuit
- Many ICs have > 100 inputs



3-input NAND

$$2^{100} = 1.27 \times 10^{30}$$

Applying 10^{30} tests at 10^9 per second (1 GHz) will require 10^{21} secs = 400 billion centuries!

- Only a very few input combinations can be applied in practice

IC Testing in Practice

For high end circuits

- A few seconds of test time on very expensive production testers
 - Many thousand test patterns applied
 - Test patterns carefully chosen to detect likely faults
 - High economic impact
 - test costs are approaching manufacturing costs
- Despite the costs, testing is always imperfect!**

How well must we test?

Approximate order of magnitude estimates

- **Number of parts per typical system: 100**
 - **Acceptable system defect rate: 1% (1 per 100)**
 - **Therefore, required part reliability**
 - 1 defect in 10,000**
 - 100 Defects Per Million (100 DPM)**
- Requirement ~100 DPM for commercial ICs**
- ~1000 DPM for ASICs**
- “Zero Defect” target for automotive**

How well must we test?

Assume 2 million ICs manufactured with
50% yield

- ❖ 1 million GOOD >> shipped
- ❖ 1 million BAD >> test escapes cause defective parts to be shipped
- ❖ For 100 BAD parts in 1M shipped (DPM=100)
Test must detect 999,900
out of the 1,000,000 BAD

For 100 DPM: Needed Test Coverage = 99.99%

DPM and System Failure Probability

Defective Parts per Million parts shipped:

- **~ 100 DPM (0.01%) for commercial ICs**
 - **System with 10 ICs => 0.1% Failure Probability**
 - **System with 100 ICs => 1.0% Failure Probability**
 - **System with 500 ICs => 5.0% Failure Probability**
- **< 10 DPM Automotive Industry**
Target : “Zero” defects!

Classical Yield Models

Two classes of Manufacturing Defects

- ❖ **Gross or area defects**

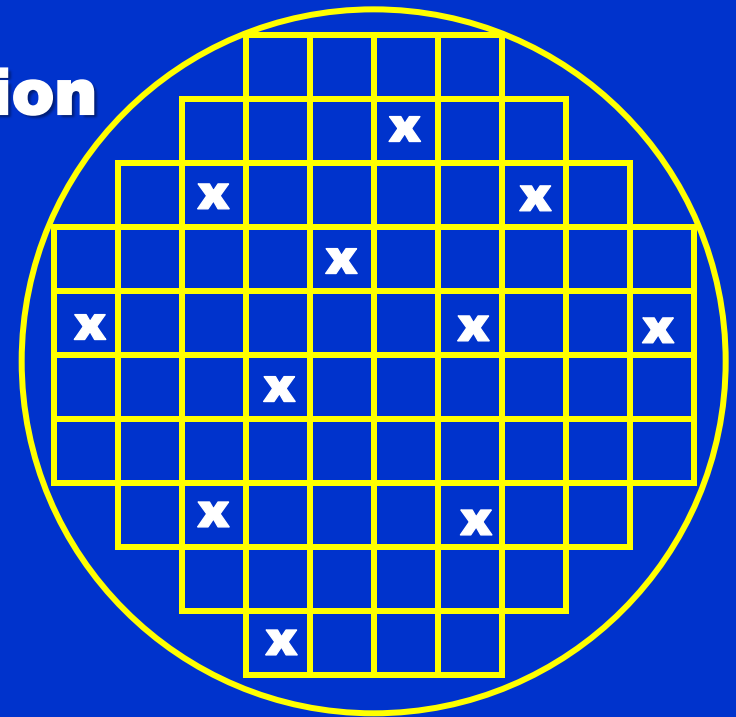
- ❖ **Random Spot Defects**

In mature well controlled processes, die yield is mostly limited by random spot defects

- impossible to completely eliminate**

Yield and Defect Density

The simplest defect distribution model for semiconductor wafers assumes that random spot defects are uniformly distributed



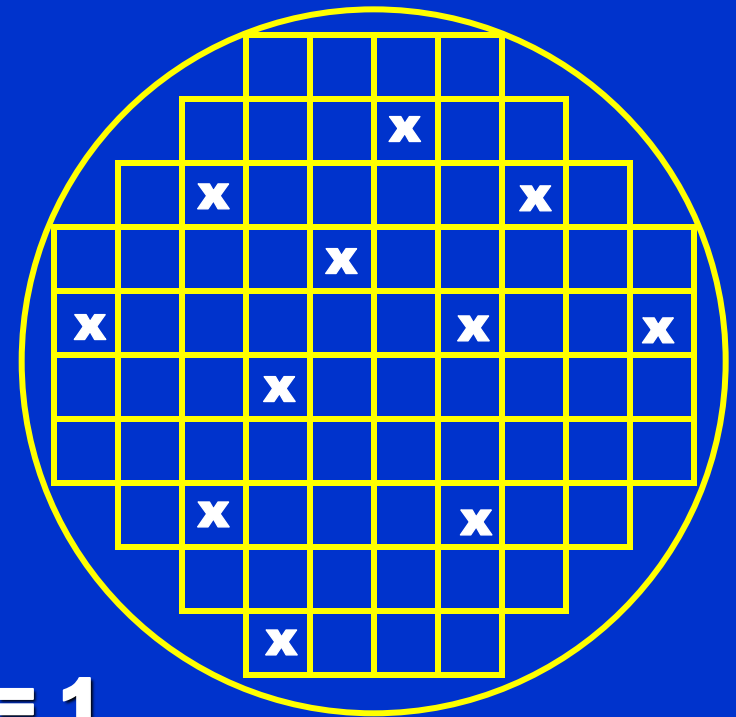
$$\text{Die Yield} = e^{-\lambda}$$

λ = Average number of defects per Die
= Defect Density ($\sim 0.2 - 1.0$ per cm^2) \times Die Area

Yield and Defect Density

Die Yield = $e^{-\lambda}$

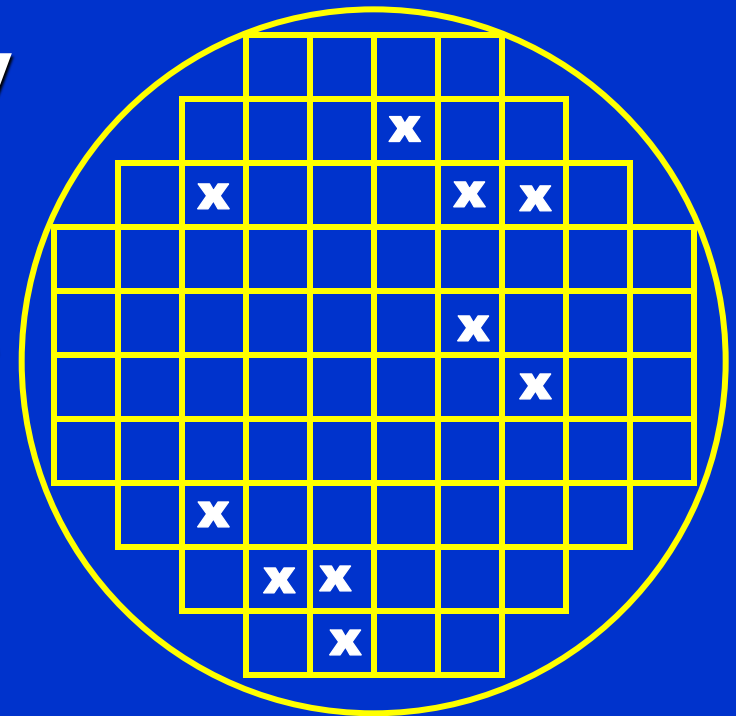
λ = **Average number
of defects per Die
= Defect Density
x Die Area**



- **Yield = 1/e (37%) for $\lambda = 1$**
- **Defect Density ~ 0.5 defects/sq cm**
- **Largest Die are ~ 2 sq cms**

Defect Clustering on Wafers

- ❖ **The Poisson model has been found to consistently underestimate yield**
- ❖ **This suggests, defects on semiconductor wafers are not uniformly distributed but are clustered**



- ❖ **For a given total number of defects on the wafer, defect clustering results in more die with multiple defects, and therefore more defect free die (higher yield)**

DPM depends on Yield

For Test Coverage: 99.99%

(Escapes 100 per million defective)

- 1 Million Parts @ 10% Yield

0.1 million GOOD >> shipped

0.9 million BAD >> 90 test escapes

DPM = 90 / 0.1 = 900

- 1 Million Parts @ 90% Yield

0.9 million GOOD >> shipped

0.1 million BAD >> 10 test escapes

DPM = 10 / 0.9 = 11

Testing Large Complex Die

Testing large, complex low yielding die is the biggest challenge

- **Higher DPM even for equally effective (similar “coverage”) tests because of lower yields**
- **Difficult to achieve high coverage testing for large complex die**
- **DPM increases non linearly with die complexity**

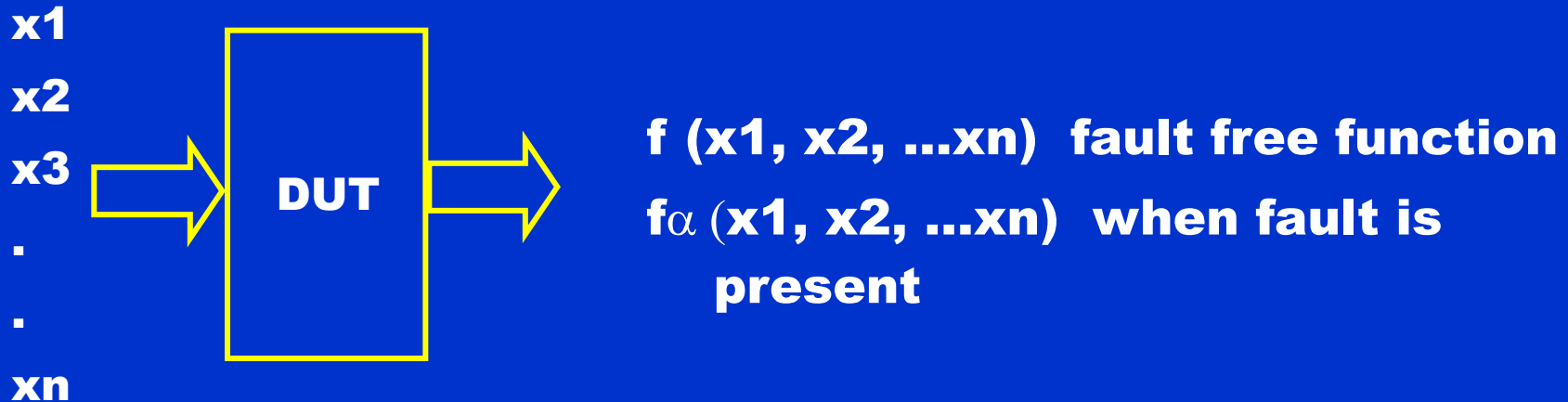
Real Defect Types

Actual manufacturing defects, flaws, variability etc. can have very complex interactions leading to unpredictable anomalous electrical behavior

- **Permanent or hard faults**
- **Difficult to achieve high coverage testing for large complex die**
- **DPM increases quite non-linearly with die complexity**

Test Basics

Test Basics



Input $(a_1, a_2, a_3 \dots a_n)$ is a test for fault α iff
 $f(a_1, a_2, a_3 \dots a_n) \neq f_\alpha(a_1, a_2, a_3 \dots a_n)$

Note: We are only interested in knowing if the DUT is faulty, not in diagnosing or locating the fault

Test Basics

For an n input circuit, there are 2^n input combinations. Ideally we must test for all possible faulty functions. This will require an exhaustive test with 2^n inputs

Since we cannot apply the exhaustive test set our best bet is to target likely faults!

x1	x2	x3	f
0	0	0	1
0	0	1	0
0	1	0	0
0	1	1	1
1	0	0	1
1	0	1	1
1	1	0	0
1	1	1	1

Test Basics

Defects Faults and Errors

A **Defect** is a physical flaw in the device, i.e. a shorted transistor or an open interconnect

A **Fault** is the logic level manifestation of the Defect, i.e. a line permanently stuck at a low logic level

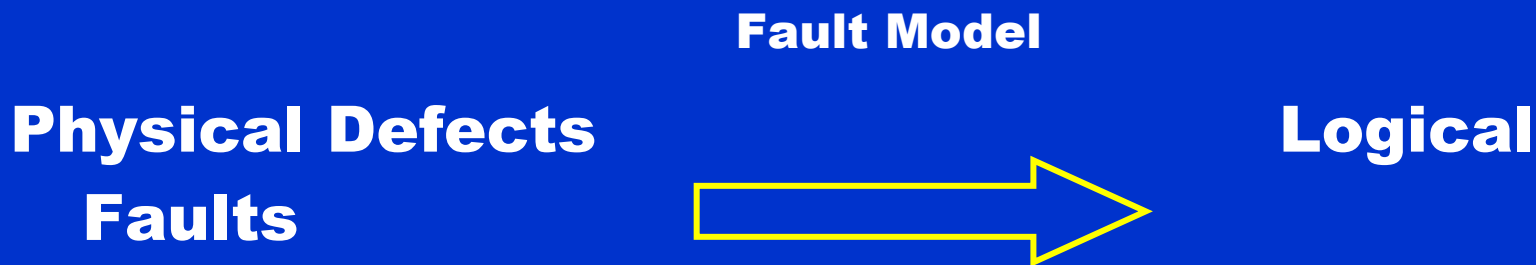
An **Error** occurs when a fault causes an incorrect logic value at a functional output

Test Basics

Likely defects

- Depend on the circuit, layout, process control
- Difficult to obtain

Simplify the problem by targeting only Logical Faults



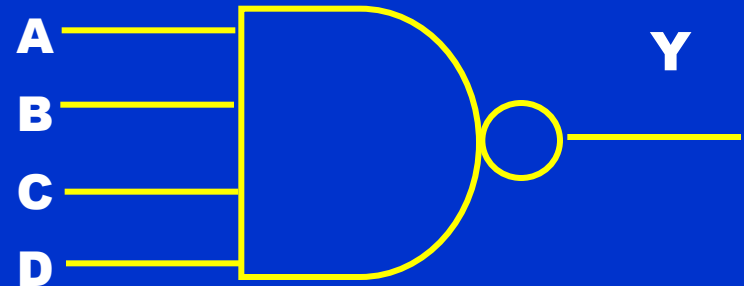
The Stuck-at Fault Model

Assumes defects cause a signal line to be permanently stuck high or stuck low

- **s-a-0** **Stuck-at 0**
- **s-a-1** **Stuck-at 1**

- **How good is this model?**
- **What does it buy us?**

Stuck-at Test for NAND4



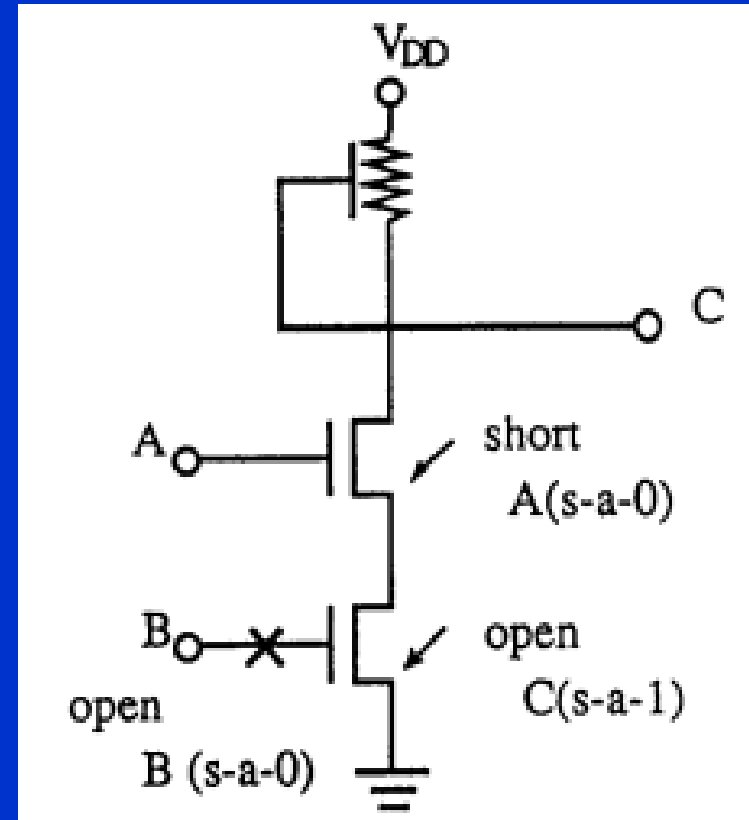
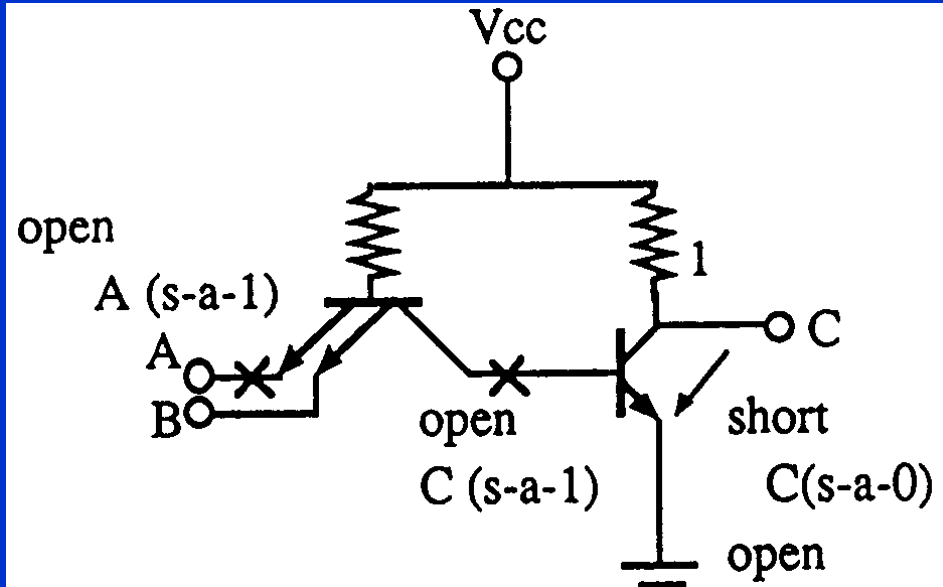
Fault List:

Possible Faults {A/0, A/1, B/0, B/1, C/0, C/1, D/0, D/1, Y/0, Y/1}

Test				Faults Detected
A	B	C	D	
1	1	1	1	A/0, B/0, C/0, D/0, Y/1
0	1	1	1	A/1, Y/0
1	0	1	1	B/1, Y/0
1	1	0	1	C/1, Y/0
1	1	1	0	D/1, Y/0

Test Set size = n+1
not 2^n

Stuck-at-fault Model



- Was reasonable for Bipolar technologies and NMOS
- Less good for CMOS